

Alexey Sherchenkov

List of Publications by Year in descending order

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112
citing authors

#	ARTICLE	IF	CITATIONS
1	Estimation of kinetic parameters for the phase change memory materials by DSC measurements. Journal of Thermal Analysis and Calorimetry, 2014, 117, 1509-1516.	3.6	21
2	Peculiarities of Bi doping of Ge ₂ Sb ₂ Te ₅ thin films for PCM devices. Canadian Journal of Physics, 2014, 92, 684-689.	1.1	20
3	Laser-induced modification and formation of periodic surface structures (ripples) of amorphous GST225 phase change materials. Optics and Laser Technology, 2019, 113, 87-94.	4.6	18
4	Thermal properties of phase change material Ge ₂ Sb ₂ Te ₅ doped with Bi. Journal of Non-Crystalline Solids, 2013, 377, 26-29.	3.1	17
5	Effect of doping on the crystallization kinetics of phase change memory materials on the basis of Ge ₂ Sb ₂ Te ₅ system. Journal of Thermal Analysis and Calorimetry, 2017, 127, 283-290.	3.6	15
6	Thermal effects in Ge-Sb-Te phase-change memory materials during multiple thermal cycling. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, NA-NA.	0.8	14
7	Specific Features of Formation of Laser-Induced Periodic Surface Structures on Ge ₂ Sb ₂ Te ₅ Amorphous Thin Films under Illumination by Femtosecond Laser Pulses. Physica Status Solidi (B): Basic Research, 2020, 257, 1900617.	1.5	13
8	Low power reconfigurable multilevel nanophotonic devices based on Sn-doped Ge ₂ Sb ₂ Te ₅ thin films. Acta Materialia, 2022, 234, 117994.	7.9	11
9	The influence of compression conditions on the peculiarities of self-propagating exothermal reaction in Al-Ni powder reactive materials. Journal of Thermal Analysis and Calorimetry, 2018, 134, 35-44.	3.6	5
10	Influence of the Degree of Crystallinity on the Dispersion of the Optical Parameters of Ge ₂ Sb ₂ Te ₅ Phase-Change Memory Thin Films. Semiconductors, 2020, 54, 1775-1783.	0.5	4
11	The Influence of Materials of Electrodes of Sensitized Solar Cells on Their Capacitive and Electrical Characteristics. Russian Physics Journal, 2018, 61, 196-202.	0.4	3
12	Influence of the adjacent layers on the crystallization kinetics of Ge ₂ Sb ₂ Te ₅ thin films. Journal of Thermal Analysis and Calorimetry, 2020, 142, 1019-1029.	3.6	3
13	Kinetics of volume and surface driven crystallization in thin films. Journal of Physics Condensed Matter, 2020, 32, 355401.	1.8	3
14	Electrophysical Properties of Ge ₂ Sb ₂ Te ₅ Thin Films for Phase Change Memory Devices. Russian Physics Journal, 2017, 59, 1417-1424.	0.4	2
15	Electrical properties and transport mechanisms in phase change memory thin films of quasi-binary-line GeTe ₂ Sb ₂ Te ₃ chalcogenide semiconductors. Semiconductors, 2017, 51, 146-152.	0.5	2
16	The vacuum arc ion source for indium and tin ions implantation into phase change memory thin films. Review of Scientific Instruments, 2019, 90, 123313.	1.3	2
17	Integral isoconversional method for evaluating crystallization parameters of thin films of Ge ₂ Sb ₂ Te ₅ phase change memory materials. Inorganic Materials, 2017, 53, 45-49.	0.8	1
18	Multiple thermal cycling and phase transitions in Ge-Sb-Te materials. Journal of Non-Crystalline Solids, 2018, 501, 101-105.	3.1	1

#	ARTICLE	IF	CITATIONS
19	Characteristics of Amorphous As ₂ S ₃ Semiconductor Films Obtained via Spin Coating. Semiconductors, 2018, 52, 1963-1968.	0.5	1